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ABSTRACT

A method of manufacturing a semiconductor device comprises: a first step of interposing a thermosetting anisotropic conductive material 16 between a substrate 12 and a semiconductor chip 20; a second step in which pressure and heat are applied between the semiconductor chip 20 and the substrate 12, an interconnect pattern 10 and electrodes 22 are electrically connected, and the anisotropic conductive material 16 is spreading out beyond the semiconductor chip 20 and is cured in the region of contact with the semiconductor chip 20; and a third step in which the region of the anisotropic conductive material 16 other than the region of contact with the semiconductor chip 20 is heated.

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